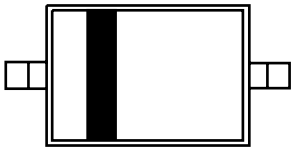
YEA SHIN TECHNOLOGY CO., LTD

RB751G-40

Schottky barrier diode

SOD– 723



●Applications

General rectification

●Features

1) Small power mold type.
(SOD-723)
2) Low V_F
3) High reliability

●Construction

Silicon epitaxial planar

●DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
RB751G-40	5	4000/Tape&Reel

●Absolute maximum ratings (Ta=25°C)

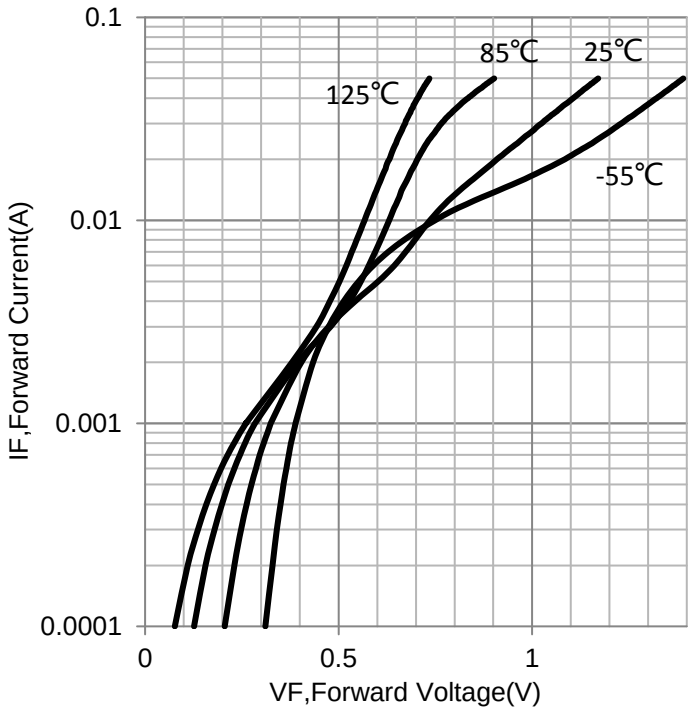
Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	40	V
Reverse voltage (DC)	V_R	30	V
Average rectified forward current	Io	30	mA
Forward current surge peak（60Hz・1cyc）	I_{FSM}	200	mA
Junction temperature	Tj	125	℃
Storage temperature	Tstg	-40 to +125	℃

●Electrical characteristic (Ta=25°C)

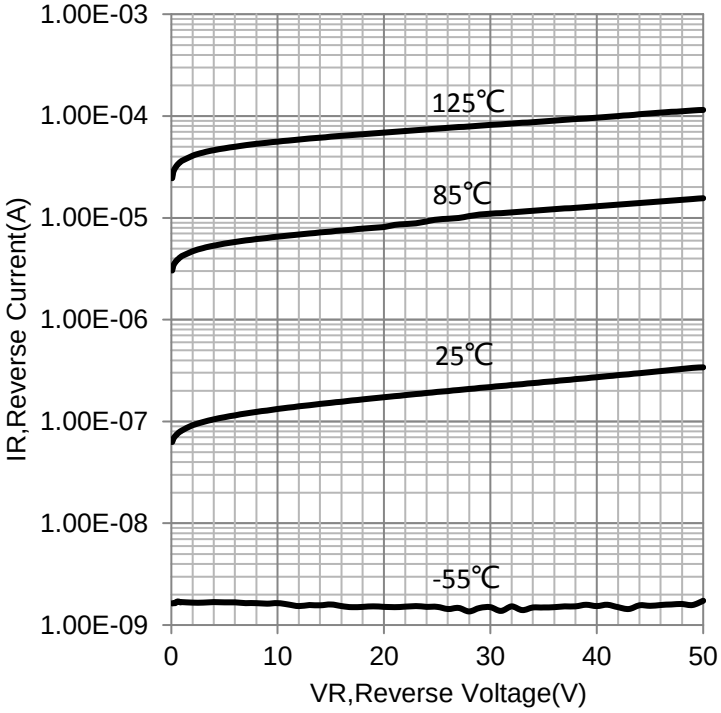
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	0.37	V	I_F=1mA
Reverse current	I_R	-	-	0.5	μA	V_R=30V
Capacitance between terminals	Ct	-	2	-	pF	V_R=1V , f=1MHz

DEVICE CHARACTERISTICS

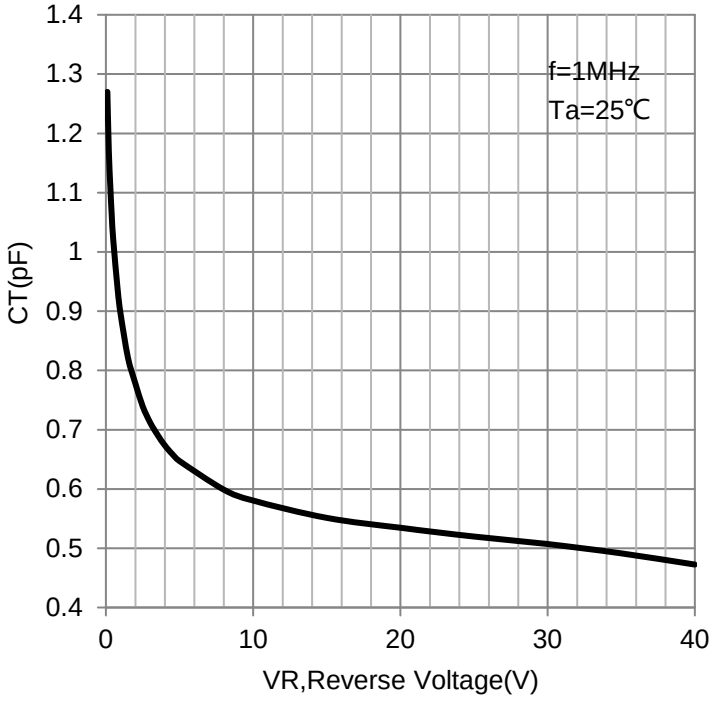
RB751G-40



IF vs. VF



IR vs. VR

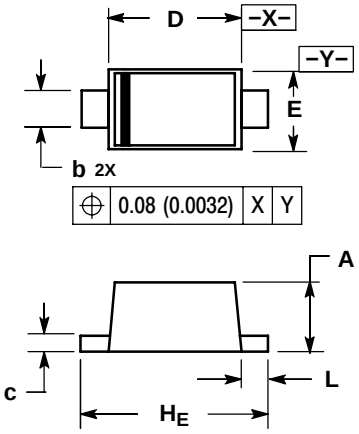


CT vs. VR

PACKAGE OUTLINE & DIMENSIONS

RB751G-40

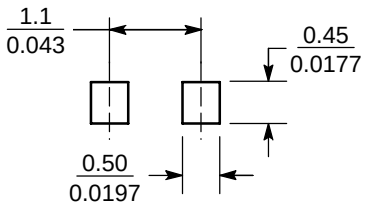
SOD−723



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.49	0.52	0.55	0.019	0.020	0.022
b	0.25	0.28	0.32	0.0098	0.011	0.013
c	0.08	0.12	0.15	0.0032	0.0047	0.0059
D	0.95	1.00	1.05	0.037	0.039	0.041
E	0.55	0.60	0.65	0.022	0.024	0.026
H_E	1.35	1.40	1.45	0.053	0.055	0.057
L	0.15	0.20	0.25	0.006	0.0079	0.010

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{mm}{inches}\right)$